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(71) Applicants: SYMETRIX CORPORATION [US/US]; Suite 100, 5055 Mark Dabling Boulevard, Colorado Springs, CO 80918 (US). MATSUSHITA ELECTRONICS CORPORATION [JP/JP]; 1-1, Saiwaicho, Takasuki City, Osaka Prefecture 569 (JP).

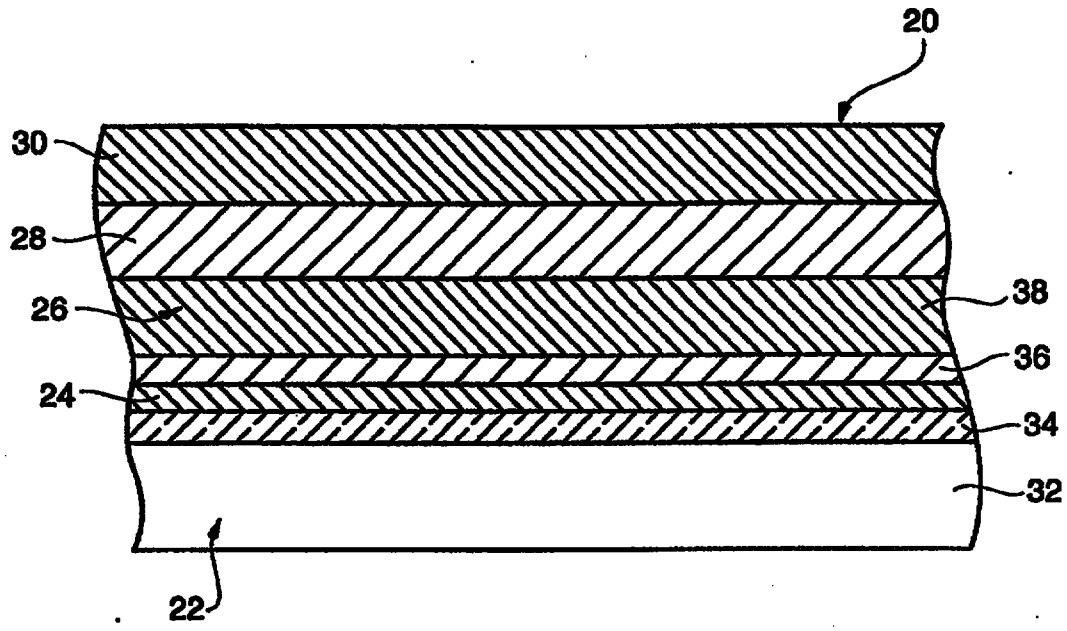
(72) Inventors: AZUMA, Masamichi; 1-3-5-502, Wakayamadai, Shimamoto-cho, Mishima-gun, Osaka 618 (JP). PAZ DE ARAUJO, Carlos, A.; 317 W. Sunbird Cliffs Lane, Colorado Springs, CO 80919 (US). CUCHIARO, Joseph, D.; 2545 Rossmere Street, Colorado Springs, CO 80919 (US).

(74) Agents: DUFT, Donald, M. et al.; Duft, Graziano & Forest, P.C., Suite 140, 1790-30th Street, Boulder, CO 80301-1018 (US).

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(54) Title: INTEGRATED CIRCUIT COMPRISING A SUBSTRATE AND A WIRING LAYER WITH A BUFFER LAYER BETWEEN THE SUBSTRATE AND THE WIRING LAYER



(57) Abstract

A thin-film ferroelectric capacitor (20) includes a bottom electrode structure (26) having an adhesion metal layer (36) and a noble metal portion (38). The electrode (26) is deposited over a thin-film buffer layer (24), which contains a layered superlattice material. The buffer layer is interposed between a substrate (22) and the bottom electrode (26). A process of manufacture includes deposition of a liquid precursor on the substrate (22) prior to formation of the bottom electrode (26).